Silicon Power Transistors

The MJL21193 and MJL21194 utilize Perforated Emitter technology and are specifically designed for high power audio output, disk head positioners and linear applications.

- Total Harmonic Distortion Characterized
- High DC Current Gain hFE = 25 Min @ IC = 8 Adc
- Excellent Gain Linearity
- High SOA: 2.25 A, 80 V, 1 Second

PNP MJL21193* NPN MJL21194*

*Motorola Preferred Device

16 AMPERE
COMPLEMENTARY
SILICON POWER
TRANSISTORS
250 VOLTS
200 WATTS



CASE 340G-02 TO-3PBL

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|-----------------------------------|--------------|---------------|
| Collector–Emitter Voltage | VCEO | 250 | Vdc |
| Collector–Base Voltage | V _{СВО} | 400 | Vdc |
| Emitter-Base Voltage | V _{EBO} | 5 | Vdc |
| Collector–Emitter Voltage – 1.5 V | VCEX | 400 | Vdc |
| Collector Current — Continuous Peak (1) | IC | 16 30 | Adc |
| Base Current – Continuous | IB | 5 | Adc |
| Total Power Dissipation @ T _C = 25°C Derate Above 25°C | PD | 200 1.43 | Watts W/°C |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | - 65 to +150 | °C |

THERMAL CHARACTERISTICS

| | Characteristic | | Max | Unit |
|----|-------------------------------------|-----------------|-----|------|
| Tł | hermal Resistance, Junction to Case | $R_{\theta JC}$ | 0.7 | °C/W |

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Typical | Max | Unit |
|--|-----------|-----|---------|-----|------|
| OFF CHARACTERISTICS | | | | | |
| Collector–Emitter Sustaining Voltage (I _C = 100 mAdc, I _B = 0) | VCEO(sus) | 250 | _ | _ | Vdc |
| Collector Cutoff Current (V _{CE} = 200 Vdc, I _B = 0) | ICEO | _ | _ | 100 | μAdc |

⁽¹⁾ Pulse Test: Pulse Width = $5.0 \,\mu s$, Duty Cycle $\leq 10\%$.

(continued)

Preferred devices are Motorola recommended choices for future use and best overall value.



MJL21193 MJL21194

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

| Characteristic | | Symbol | Min | Typical | Max | Unit |
|---|-----------------------------|---------------------|-------------|---------|----------|------|
| OFF CHARACTERISTICS | | • | | | | |
| Emitter Cutoff Current (VCE = 5 Vdc, IC = 0) | | I _{EBO} | _ | _ | 100 | μAdc |
| Collector Cutoff Current (V _{CE} = 250 Vdc, V _{BE(off)} = 1.5 Vdc) | | ICEX | _ | _ | 100 | μAdc |
| SECOND BREAKDOWN | | • | | | | |
| Second Breakdown Collector Current with Base Form (VCE = 50 Vdc, t = 1 s (non-repetitive) (VCE = 80 Vdc, t = 1 s (non-repetitive) | ward Biased | IS/b | 4.0 2.25 | | _ _ | Adc |
| ON CHARACTERISTICS | | • | | | | |
| DC Current Gain (I _C = 8 Adc, V _{CE} = 5 Vdc) (I _C = 16 Adc, I _B = 5 Adc) | | hFE | 25 8 | _ _ | 75 — | |
| Base–Emitter On Voltage (I _C = 8 Adc, V _{CE} = 5 Vdc) | | V _{BE(on)} | _ | _ | 2.2 | Vdc |
| Collector–Emitter Saturation Voltage (I _C = 8 Adc, I _B = 0.8 Adc) (I _C = 16 Adc, I _B = 3.2 Adc) | | VCE(sat) | _ _ _ | | 1.4 4 | Vdc |
| DYNAMIC CHARACTERISTICS | | • | | • | | |
| Total Harmonic Distortion at the Output V _{RMS} = 28.3 V, f = 1 kHz, P _{LOAD} = 100 W _{RMS} | hFE | THD | | 0.0 | | % |
| (Matched pair hFE = 50 @ 5 A/5 V) | unmatched hFE matched | | _ _ | 0.8 | _ | |
| Current Gain Bandwidth Product (I _C = 1 Adc, V _{CE} = 10 Vdc, f _{test} = 1 MHz) | | fT | 4 | _ | _ | MHz |
| Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f _{test} = 1 MHz) | | C _{ob} | _ | _ | 500 | pF |

⁽¹⁾ Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤2%

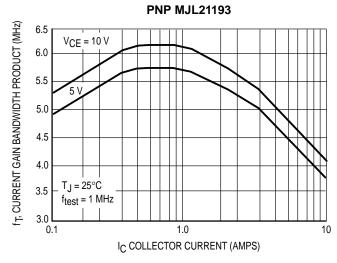


Figure 1. Typical Current Gain Bandwidth Product

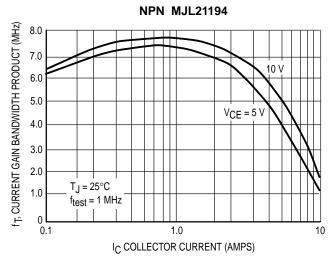


Figure 2. Typical Current Gain Bandwidth Product

TYPICAL CHARACTERISTICS

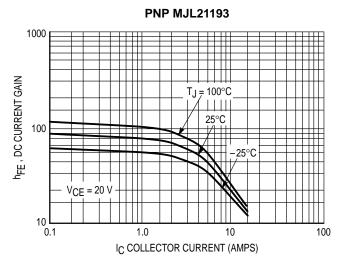


Figure 3. DC Current Gain, VCE = 20 V

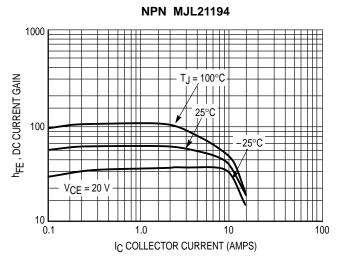


Figure 4. DC Current Gain, VCE = 20 V

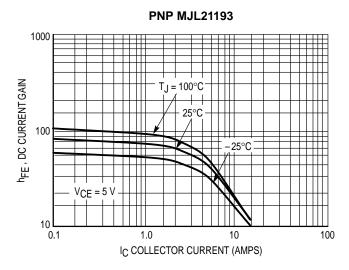


Figure 5. DC Current Gain, VCE = 5 V

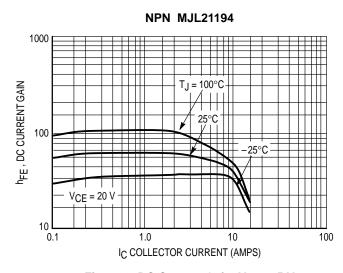


Figure 6. DC Current Gain, VCE = 5 V

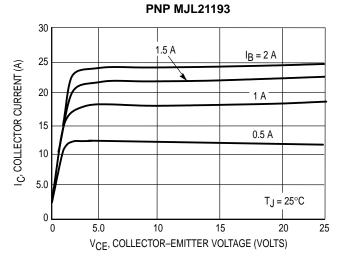


Figure 7. Typical Output Characteristics

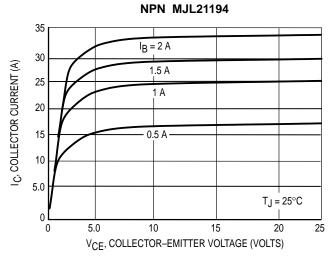


Figure 8. Typical Output Characteristics

TYPICAL CHARACTERISTICS

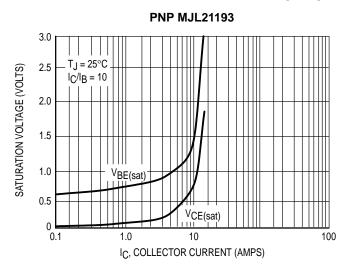


Figure 9. Typical Saturation Voltages

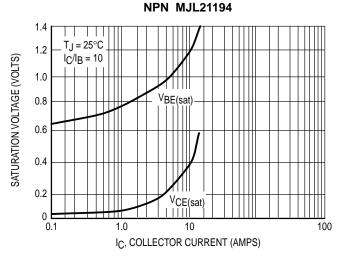


Figure 10. Typical Saturation Voltages

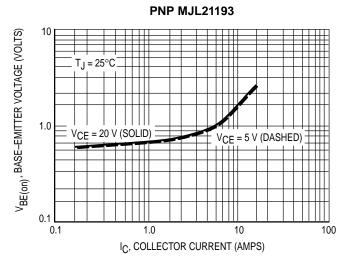


Figure 11. Typical Base–Emitter Voltage

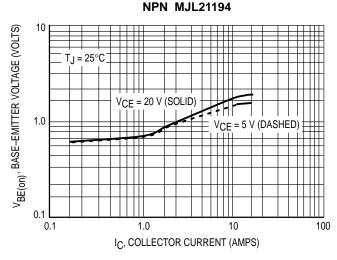


Figure 12. Typical Base-Emitter Voltage

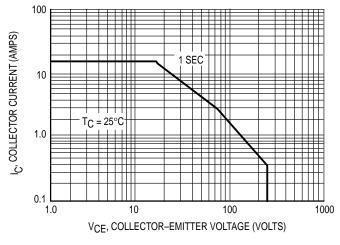


Figure 13. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate IC - VCE limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 13 is based on $T_{J(pk)} = 200^{\circ}C$; T_{C} is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

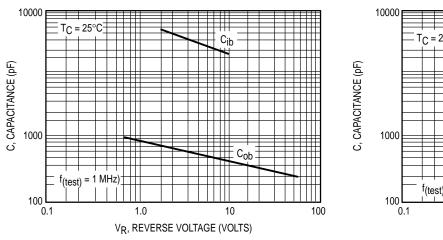


Figure 14. MJL21193 Typical Capacitance

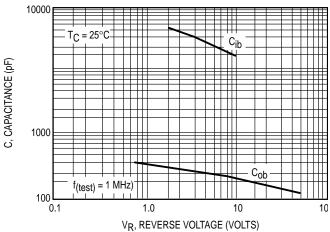


Figure 15. MJL21194 Typical Capacitance

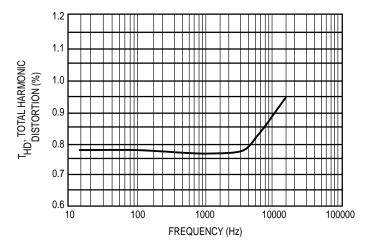


Figure 16. Typical Total Harmonic Distortion

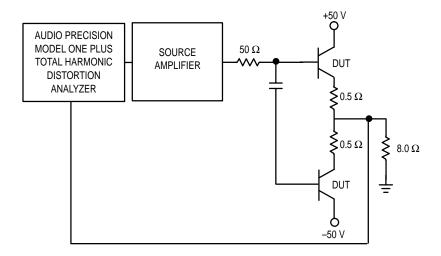
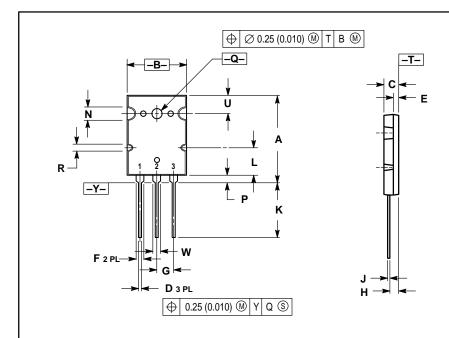


Figure 17. Total Harmonic Distortion Test Circuit

PACKAGE DIMENSIONS



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 Y14 5M 1982
- 2. CONTROLLING DIMENSION: MILLIMETER.

| | MILLIN | IETERS | INCHES | | |
|-----|----------|--------|--------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 2.8 | 2.9 | 1.102 | 1.142 | |
| В | 19.3 | 20.3 | 0.760 | 0.800 | |
| С | 4.7 | 5.3 | 0.185 | 0.209 | |
| D | 0.93 | 1.48 | 0.037 | 0.058 | |
| Е | 1.9 | 2.1 | 0.075 | 0.083 | |
| F | 2.2 | 2.4 | 0.087 | 0.102 | |
| G | 5.45 BSC | | 0.215 | BSC | |
| Н | 2.6 | 3.0 | 0.102 | 0.118 | |
| J | 0.43 | 0.78 | 0.017 | 0.031 | |
| K | 17.6 | 18.8 | 0.693 | 0.740 | |
| L | 11.0 | 11.4 | 0.433 | 0.449 | |
| N | 3.95 | 4.75 | 0.156 | 0.187 | |
| Р | 2.2 | 2.6 | 0.087 | 0.102 | |
| Q | 3.1 | 3.5 | 0.122 | 0.137 | |
| R | 2.15 | 2.35 | 0.085 | 0.093 | |
| U | 6.1 | 6.5 | 0.240 | 0.256 | |
| W | 2.8 | 3.2 | 0.110 | 0.125 | |

STYLE 2:

PIN 1. BASE 2. COLLECTOR

3. EMITTER

CASE 340G-02 TO-3PBL ISSUE E

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How to reach us:

USA/EUROPE: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036. 1–800–441–2447

MFAX: RMFAX0@email.sps.mot.com – TOUCHTONE (602) 244–6609 INTERNET: http://Design-NET.com

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki, 6F Seibu-Butsuryu-Center, 3–14–2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03–3521–8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298



